

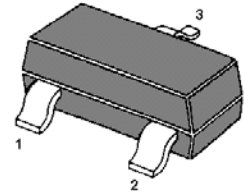
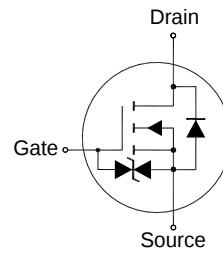
MMFTN123K-AH

N-Channel Enhancement Mode MOSFET

Features

- AEC-Q101 Qualified
- Halogen and Antimony Free(HAF),
RoHS compliant
- Typical ESD Protection HBM Class 2

Classification	Voltage Range(V)
0A	< 125
0B	125 to < 250
1A	250 to < 500
1B	500 to < 1000
1C	1000 to < 2000
2	2000 to < 4000
3A	4000 to < 8000
3B	≥ 8000



1. Gate 2. Source 3. Drain
TO-236 Plastic Package

Applications

- Portable appliances
- Low switch appliances

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$ unless otherwise specified)

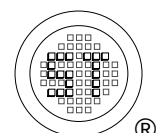
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	200	mA
Peak Drain Current, Pulsed ¹⁾	I_{DM}	600	mA
Total Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ²⁾	$R_{\theta JA}$	250	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{j(MAX)}=150^\circ\text{C}$.

²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

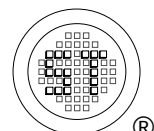


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MMFTN123K-AH

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250\ \mu\text{A}$	$V_{(BR)DSS}$	100	-	-	V
Drain-Source Leakage Current at $V_{DS} = 80\ \text{V}$	I_{DSS}	-	-	1	μA
Gate-Source Leakage Current at $V_{GS} = \pm 20\ \text{V}$	I_{GSS}	-	-	± 10	μA
Gate-Source Threshold Voltage at $V_{GS} = V_{DS}$, $I_D = 1\ \text{mA}$	$V_{GS(th)}$	1.5	-	2.5	V
Drain-Source On-State Resistance at $V_{GS} = 10\ \text{V}$, $I_D = 190\ \text{mA}$ at $V_{GS} = 4.5\ \text{V}$, $I_D = 150\ \text{mA}$	$R_{DS(ON)}$	- -	- -	6 10	Ω
DYNAMIC PARAMETERS					
Gate resistance at $V_{DS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	R_g	-	38	-	Ω
Input Capacitance at $V_{DS} = 50\ \text{V}$, $f = 1\ \text{MHz}$	C_{iss}	-	39	-	pF
Output Capacitance at $V_{DS} = 50\ \text{V}$, $f = 1\ \text{MHz}$	C_{oss}	-	10	-	pF
Reverse Transfer Capacitance at $V_{DS} = 50\ \text{V}$, $f = 1\ \text{MHz}$	C_{rss}	-	6.6	-	pF
Total Gate Charge at $V_{GS} = 10\ \text{V}$, $V_{DD} = 30\ \text{V}$, $I_D = 1\ \text{A}$	Q_g	-	1.5	-	nC
Gate-Source Charge at $V_{GS} = 10\ \text{V}$, $V_{DD} = 30\ \text{V}$, $I_D = 1\ \text{A}$	Q_{gs}	-	0.5	-	nC
Gate-Drain Charge at $V_{GS} = 10\ \text{V}$, $V_{DD} = 30\ \text{V}$, $I_D = 1\ \text{A}$	Q_{gd}	-	0.6	-	nC
Turn-On Delay Time at $V_{DD} = 50\ \text{V}$, $I_D = 190\ \text{mA}$, $V_{GS} = 10\ \text{V}$, $R_G = 6\ \Omega$	$t_{d(on)}$	-	6.5	-	ns
Turn-On Rise Time at $V_{DD} = 50\ \text{V}$, $I_D = 190\ \text{mA}$, $V_{GS} = 10\ \text{V}$, $R_G = 6\ \Omega$	t_r	-	7.5	-	ns
Turn-Off Delay Time at $V_{DD} = 50\ \text{V}$, $I_D = 190\ \text{mA}$, $V_{GS} = 10\ \text{V}$, $R_G = 6\ \Omega$	$t_{d(off)}$	-	10	-	ns
Turn-Off Fall Time at $V_{DD} = 50\ \text{V}$, $I_D = 190\ \text{mA}$, $V_{GS} = 10\ \text{V}$, $R_G = 6\ \Omega$	t_f	-	85	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 0.1\ \text{A}$, $V_{GS} = 0\ \text{V}$	V_{SD}	-	-	1.2	V



Electrical Characteristics Curves

Fig. 1 Typical Output Characteristic

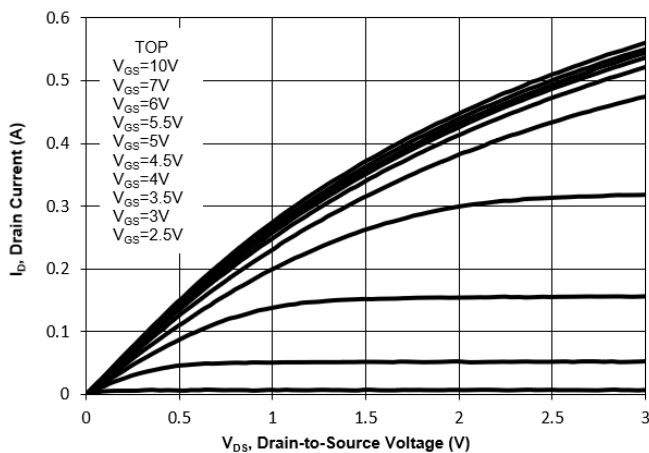


Fig. 2 Typical Transfer Characteristic

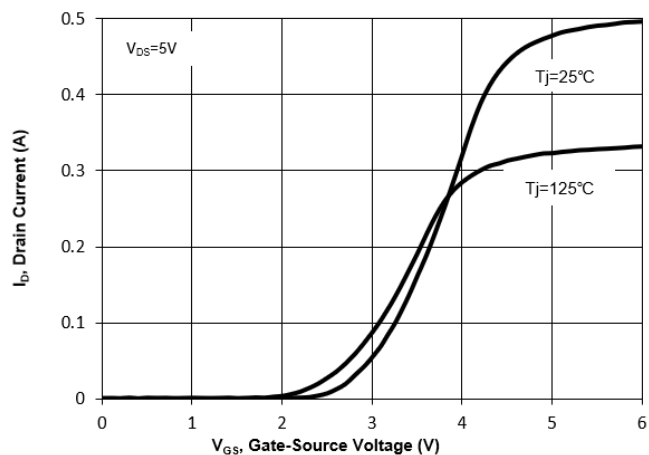


Fig. 3 on-Resistance vs Drain Current

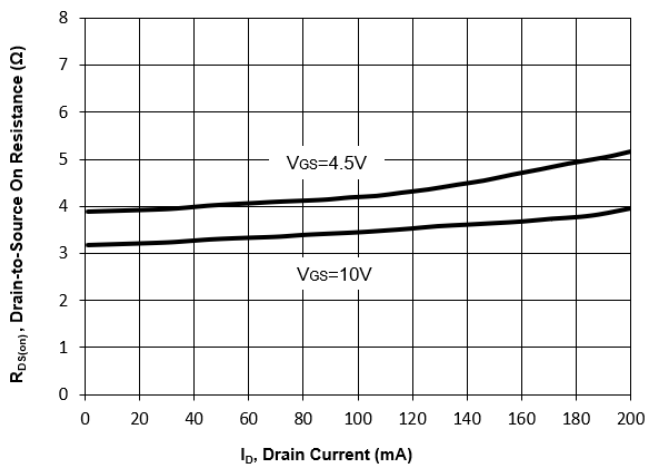


Fig. 4 on-Resistance vs. Gate Voltage

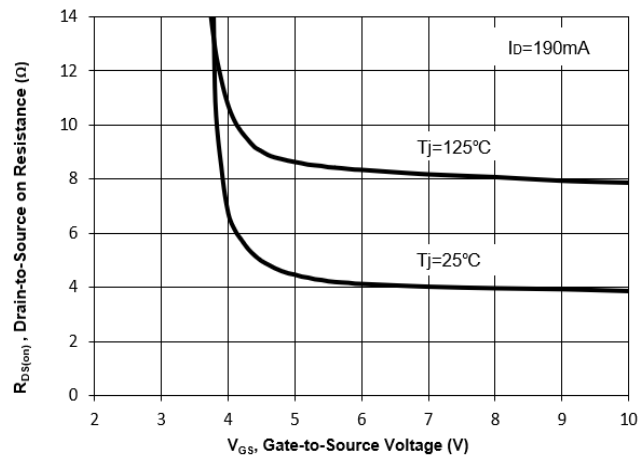


Fig. 5 on-Resistance vs. T_J

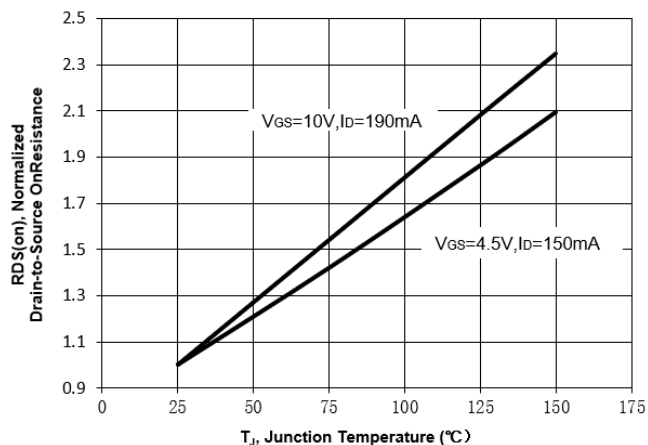
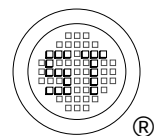
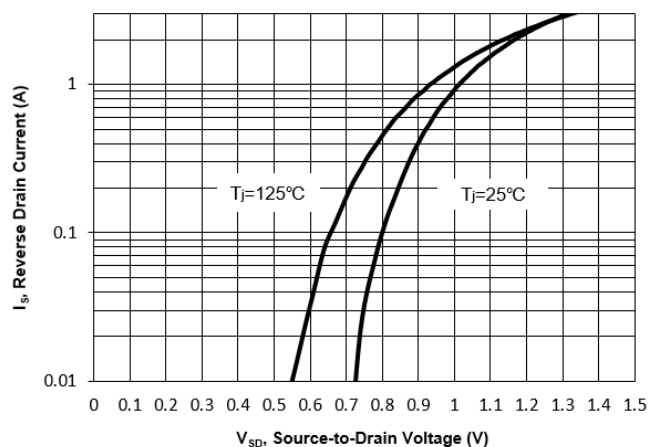


Fig. 6 Typical Forward Characteristic



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

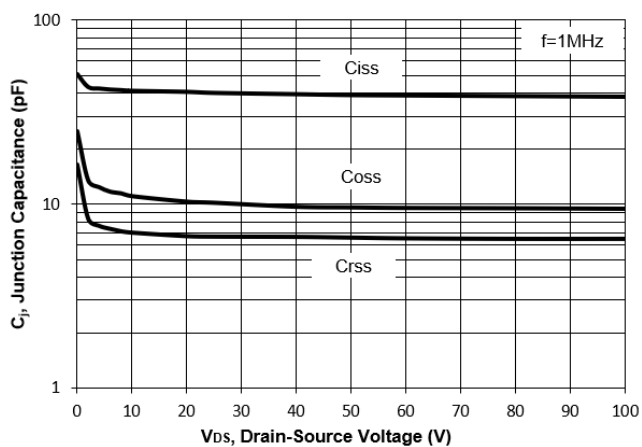


Fig. 8 Drain-Source Leakage Current vs. T_j

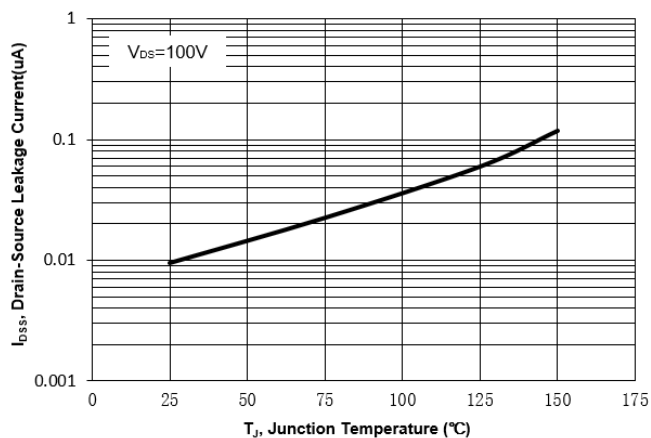


Fig. 9 $V_{(BR)DSS}$ VS. Junction Temperature

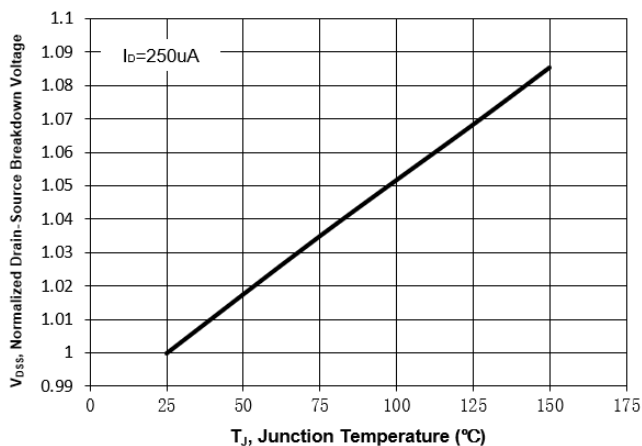


Fig. 10 Gate Threshold Variation vs. T_j

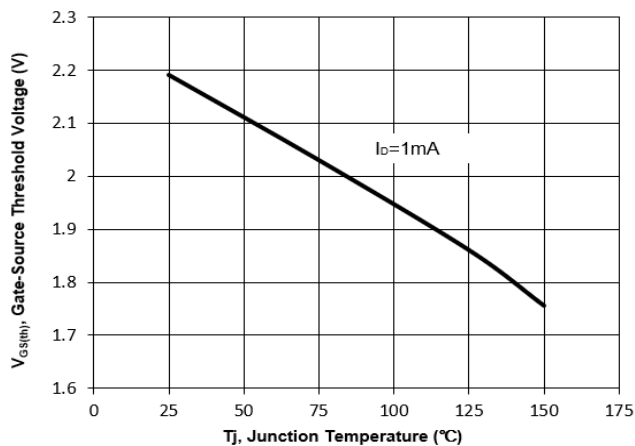
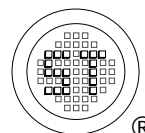
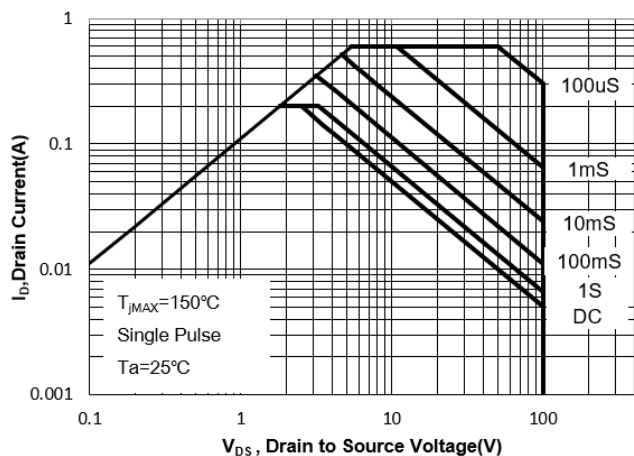


Fig. 11 Safe Operation Area



Test Circuits

Fig.1-1 Switching times test circuit

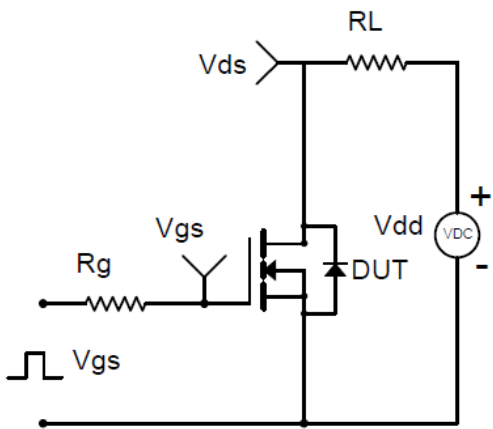


Fig.1-2 Switching Waveform

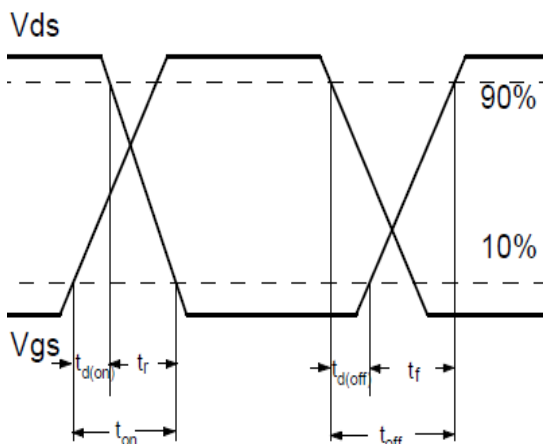


Fig.2-1 Gate charge test circuit

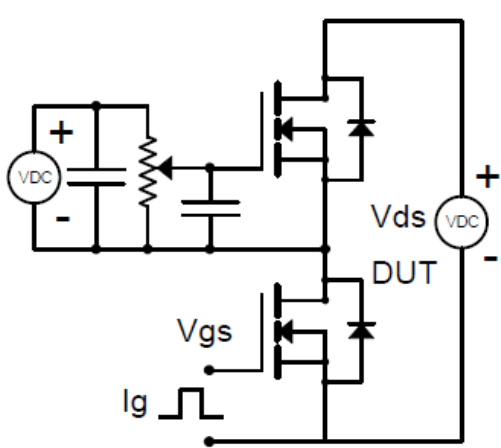
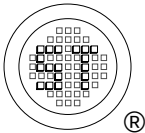
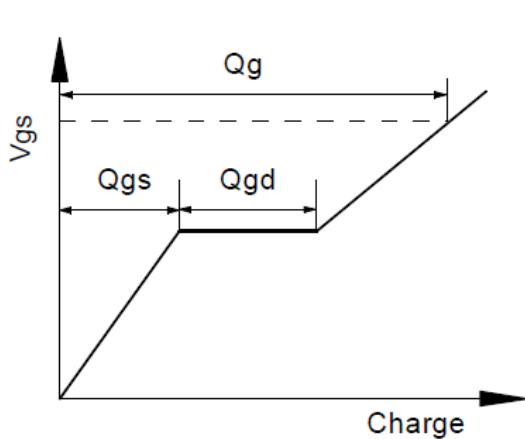


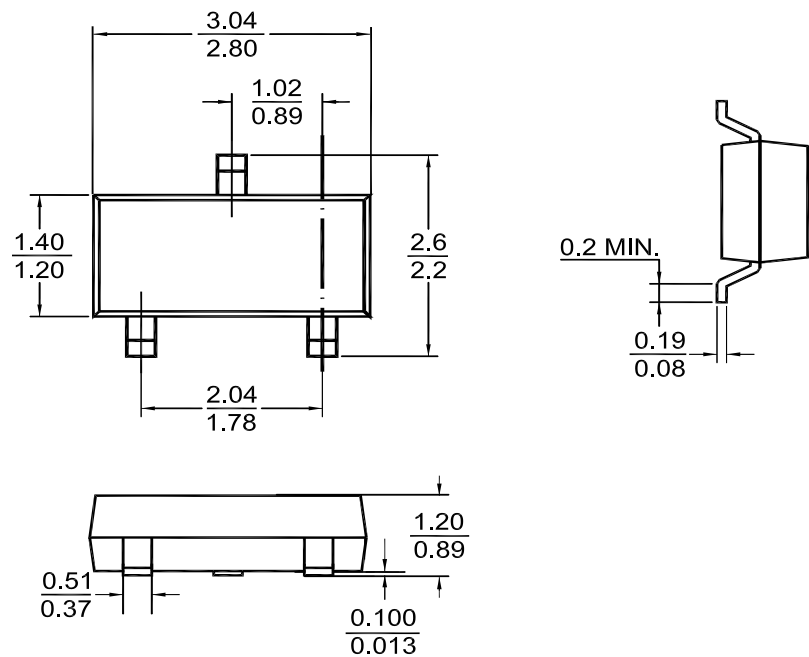
Fig.2-2 Gate charge waveform



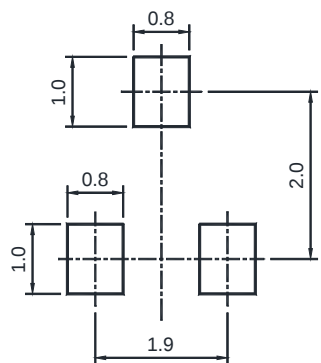
MMFTN123K-AH

Package Outline (Dimensions in mm)

TO-236



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" VZ " = Part No.
" • " = HAF (Halogen and Antimony Free)
" YM " = Date Code Marking
" Y " = Year
" M " = Month
Font type: Arial

